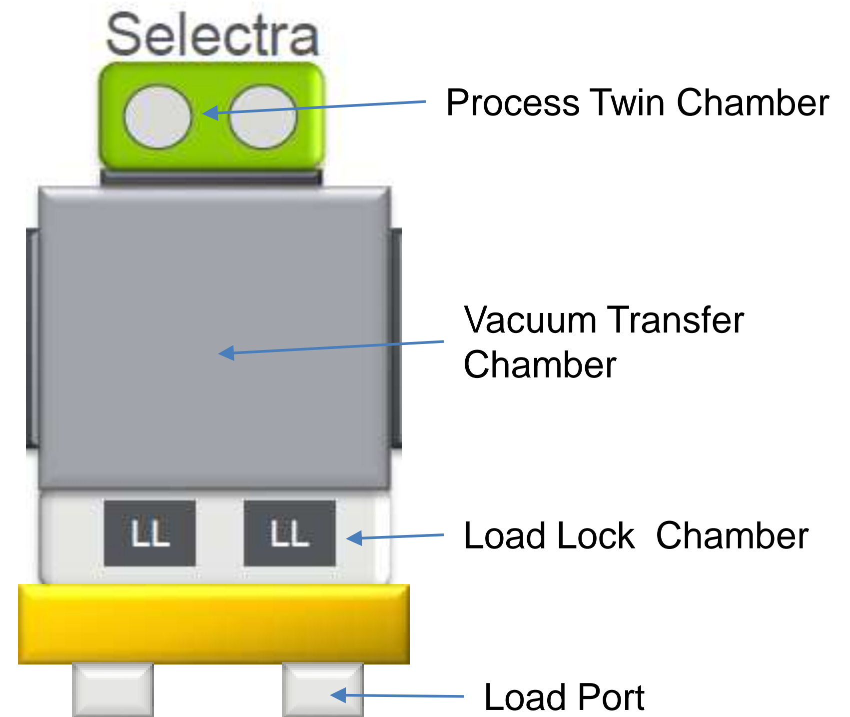
NIAR 國家實驗研究院
TSRI 台灣半導體研究中心
Taiwan Semiconductor Research Institute

12 inch High Selectivity Etcher
(AMAT Selectra Etcher)

Information

Overview



Process Module

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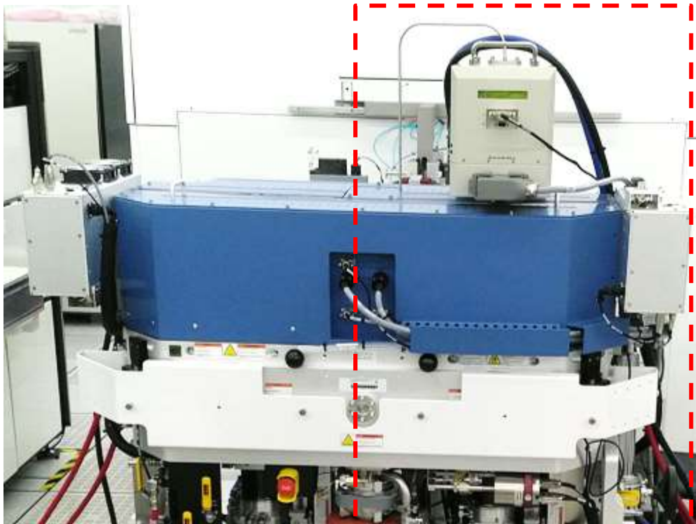
Front End Chamber Process ：



Side 1 Side 2

- Twin Chamber for Si、SiGe Etching (Side 2)

Process condition: Nano scale

Process pressure: 1torr~7torr

Process gas: NF_3、H_2

RF Top : Remote Plasma Source.

RF Bot : No

Process temperature: $15^{o}C$

Process Module

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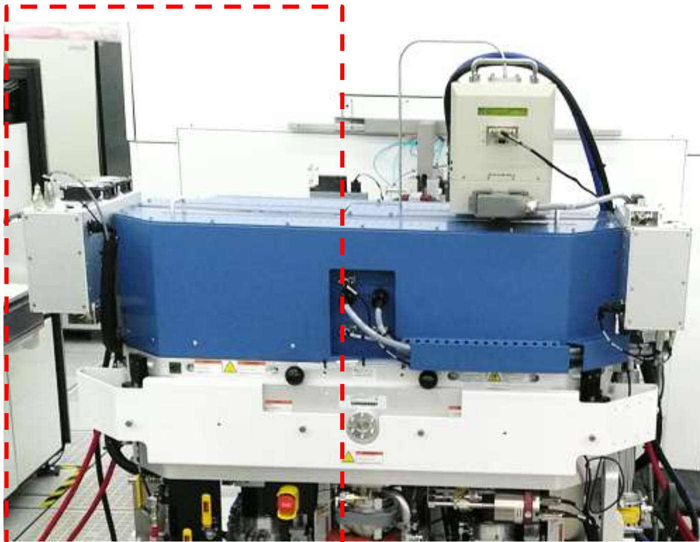

Side 1　　Side 2

Back End Chamber Process ：

- Twin Chamber for Metal polymer remove (Side 1)

Process condition: Nano scale

Process pressure: 1torr~7torr

Process gas: NF_3、H_2

RF Top : 13.56MHz、1000W

RF Bot : No

Process temperature: 80~100°C